Claim 1. (Amended)

A method for forming a junction in a semiconductor device with symmetrical halo implants, comprising the steps of:

forming a photoresist film pattern on a semiconductor substrate excluding a first region;

forming symmetrical first and second implants by performing a first halo implant process and a second halo implant process on the first region of the semiconductor substrate by using a tilt angle of about 45° and twist angles of 0° and 180° corresponding to the first halo implant and second halo implant, respectively; and

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performing a third halo implant process on the first region of the semiconductor substrate by using a tilt angle of about 0°.

Claim 2. (Amended)

The method according to claim 1, wherein both the first halo implant process and second halo implant process are performed with an energy of 20KeV and a dose of 4.0×10^{12} ions/cm^2.

Claim 4. (Amended)

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The method according to claim 1, wherein the third halo implant process is performed only once at a tilt angle of about 0°.

Claim 5. (Amended)

The method according to claim 1, wherein the third halo implant process is performed with an energy of 16KeV and a dose of 4×10^{12}.

Claim 8. (Amended)

A method for forming a junction with symmetrical halo implants in a semiconductor device, comprising the steps of:

providing a semiconductor substrate divided into a first conductive type MOS region and a second conductive type MOS region;

forming a photoresist film pattern on the second conductive type MOS region;

forming symmetrical first and second halo implants by performing first and second halo implant processes on the first conductive type MOS region at about a 45° tilt angle and at twist angles of about 0° and 180°, respectively; and

performing a third halo implant process on the first conductive type MOS region, by using a tilt angle of about 0°.

Claim 9. (Amended)

The method according to claim 8, wherein the first halo implant process is performed with an energy of 20KeV and and a dose of 4.0×10^{12} ions/cm^2.

Claim 10. (Amended)

The method according to claim 8, wherein the second halo implant process is performed with an energy of 20KeV and a dose of $4.0x10^{12}$ ions/cm^2.

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Claim 11. (Amended)

The method according to claim 8, wherein the third halo implant process is performed with an energy of 16KeV and a dose of $4x10^{12}$ ions/cm^2.

Please add the following new claims:

--14. The method of claim 1, wherein the first and second halo implants are homogenously doped.

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15. The method of claim 8, wherein the first and second halo implants are homogenously doped.--